N-Channel 30-V (D-S) MOSFET

Key Features:

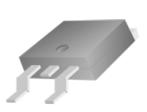
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

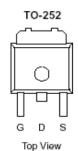
Typical Applications:

- DC/DC Conversion
- Power Routing
- Motor Drives

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)		
30	$7.5 @ V_{GS} = 4.5V$	67		
	$10 @ V_{GS} = 2.5V$	58		







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter			Limit	Units	
Drain-Source Voltage			30	V	
Gate-Source Voltage		V_{GS}	±12	V	
tinuous Drain Current ^a T _C =25°C I _D		I _D	67	А	
Pulsed Drain Current ^b		I _{DM}	260	Α	
Continuous Source Current (Diode Conduction) a	T _C =25°C	I _S	48	Α	
Power Dissipation ^a	T _C =25°C	P_D	50	W	
Operating Junction and Storage Temperature Range			-55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{ heta JC}$	3	C/VV		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

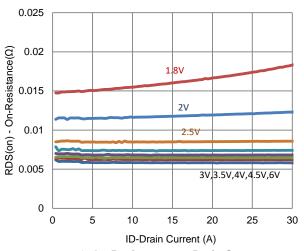
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	0.4			V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	50			Α	
Drain-Source On-Resistance ^a	r	$V_{GS} = 4.5 \text{ V}, I_{D} = 20 \text{ A}$			7.5	mΩ	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 16 \text{ A}$			10		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10 \text{ V}, I_{D} = 20 \text{ A}$		71		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 20 A, V _{GS} = 0 V		0.92		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		13			
Gate-Source Charge	Q_gs	$I_{DS} = 13 \text{ V}, \text{ V}_{GS} = 4.3 \text{ V},$ $I_{D} = 20 \text{ A}$		2.8		nC	
Gate-Drain Charge	Q_gd	1 _D = 25 / X		4.5			
Turn-On Delay Time	$t_{d(on)}$	V 45 V D = 0.9 O		11			
Rise Time	t _r	$V_{DS} = 15 \text{ V}, R_{L} = 0.8 \Omega,$ $I_{D} = 20 \text{ A}.$		22		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		47		ns	
Fall Time	t _f	v GEN = 4.5 v, r GEN 0 12		26			
Input Capacitance	C_{iss}			902			
Output Capacitance	C _{oss}	$V_{DS} = 50, V_{GS} = 0 V, f = 1 Mhz$		354		pF	
Reverse Transfer Capacitance	C_{rss}			46			

Notes

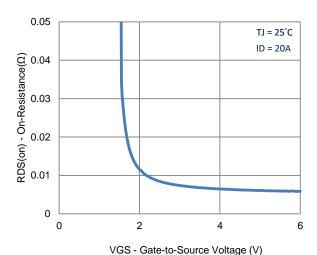
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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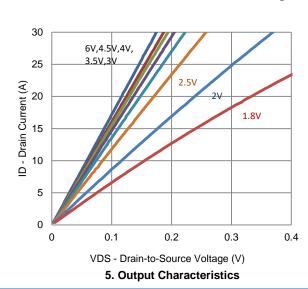
Typical Electrical Characteristics

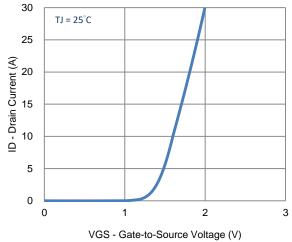


1. On-Resistance vs. Drain Current

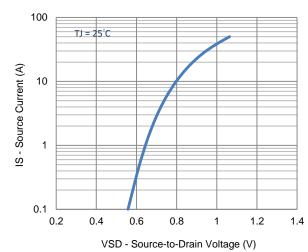


3. On-Resistance vs. Gate-to-Source Voltage

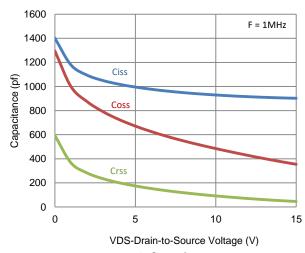




2. Transfer Characteristics

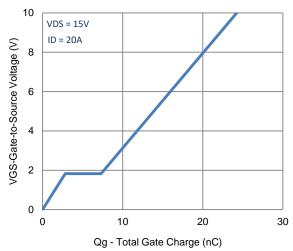


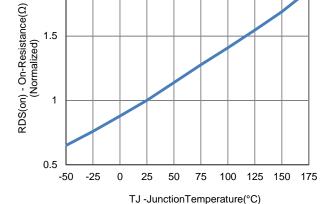
4. Drain-to-Source Forward Voltage



Typical Electrical Characteristics

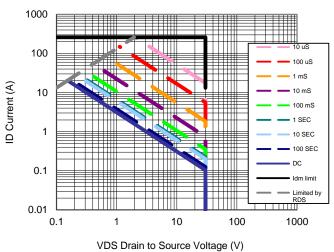
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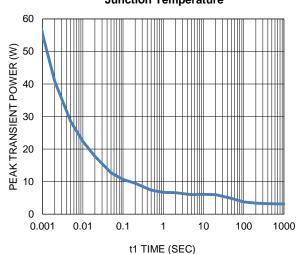




7. Gate Charge

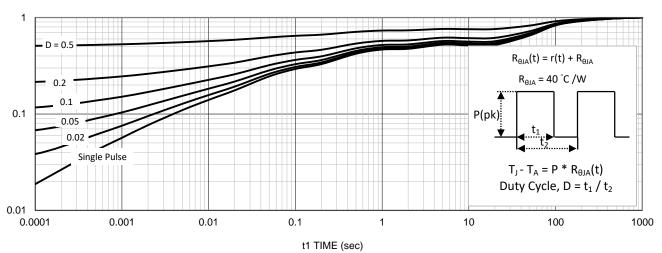
8. Normalized On-Resistance Vs Junction Temperature



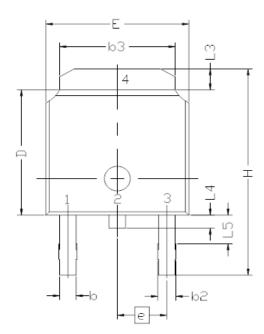


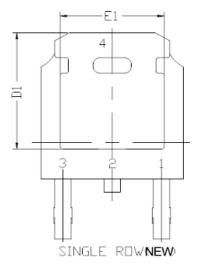
9. Safe Operating Area

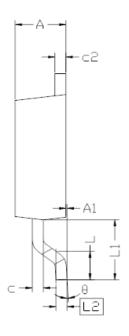
10. Single Pulse Maximum Power Dissipation



Package Information







CVMDEI	DIMENS:	[DNAL	REQMTS
SYMBOL	MIN	NDM	MAX
E	6.40	6,60	6.731
L	1.40	1.52	1.77
L1			ĖF
L2	0.	.508 BS	-
L3	0.89		1.27
L4	0.64		1.01
L5			
D	6.00	6.10	6,223
Н	9.40	10.00	10.40
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
е		286 B3	
Α	2,20	2,30	2,38
A1	0		0.127
_	0.45	0.50	0.60
c2	0.45	0,50	0.58
D1	5.30		
E1	4.40		
θ	0°		10°

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.